



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

- $BV_{CEO} > 45V$
- Ultra-Small Surface Mount Package
- Ideally Suited for Automated Insertion
- For switching and AF Amplifier Application

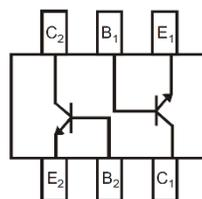
Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Finish. Solderable per MIL-STD-202, Method 208 
- Weight: 0.006 grams (Approximate)

SOT363



Top View



Device Schematic

Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$ unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	45	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	100	mA
Peak Pulse Collector Current	I_{CM}	200	mA
Peak Pulse Base Current	I_{BM}	200	mA

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$ unless otherwise specified.)

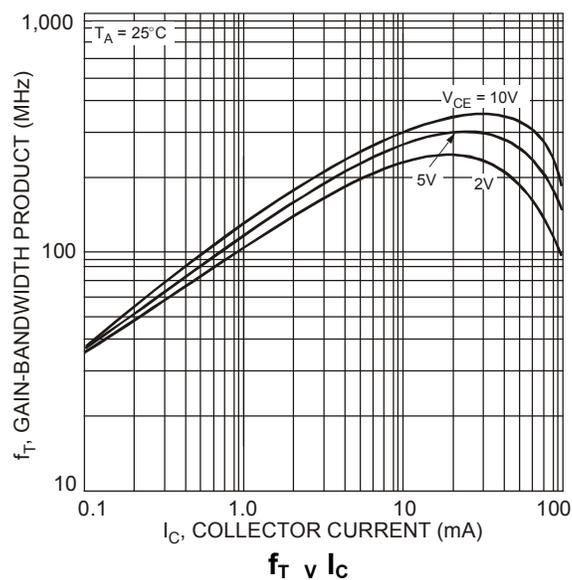
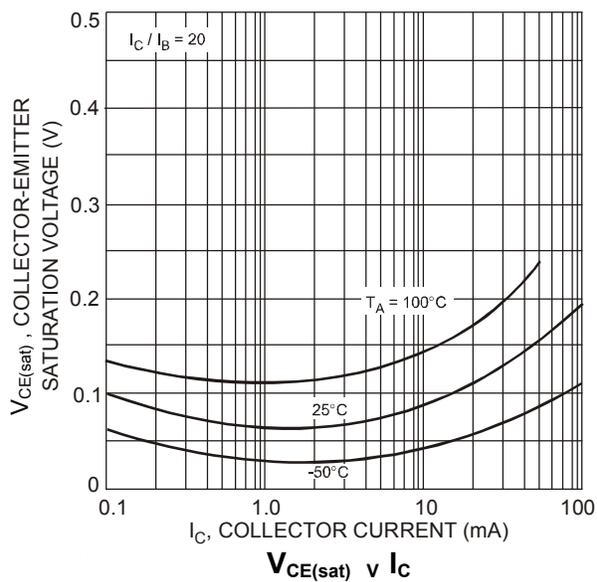
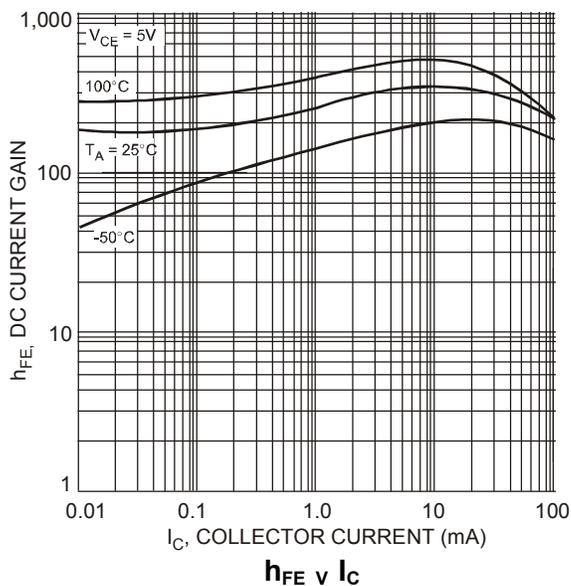
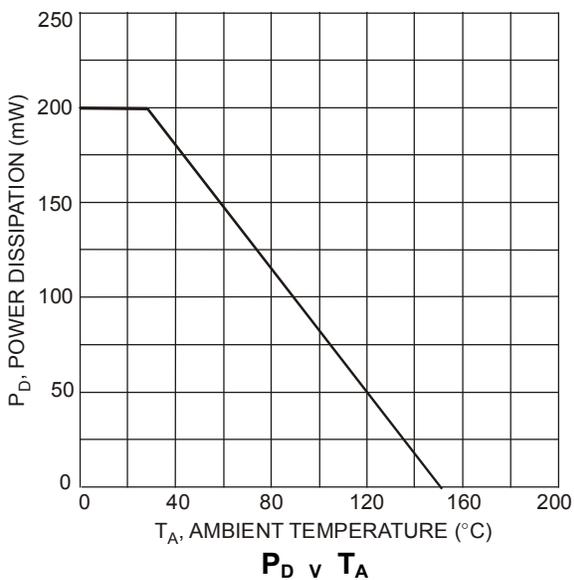
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	200	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$ unless otherwise specified.)

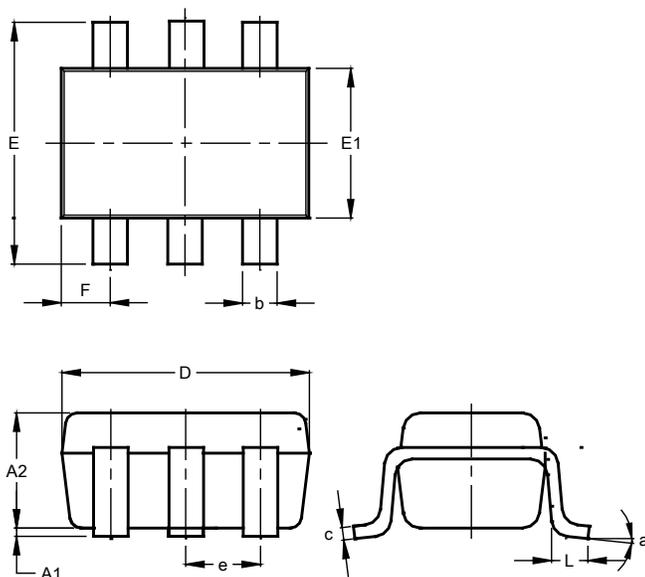
Characteristic (Note 6)	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	50	—	—	V	$I_C = 100\mu\text{A}, I_B = 0$
Collector-Emitter Breakdown Voltage	BV_{CEO}	45	—	—	V	$I_C = 10\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	6	—	—	V	$I_E = 100\mu\text{A}, I_C = 0$
DC Current Gain	h_{FE}	200	—	450	—	$V_{CE} = 5.0\text{V}, I_C = 2.0\text{mA}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	—	100 400	mV	$I_C = 10\text{mA}, I_B = 0.5\text{mA}$ $I_C = 100\text{mA}, I_B = 5.0\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	—	755	—	mV	$I_C = 10\text{mA}, I_B = 0.5\text{mA}$
Base-Emitter Voltage	$V_{BE(on)}$	580	665	700	mV	$V_{CE} = 5.0\text{V}, I_C = 2.0\text{mA}$
Collector-Cut Off Current	I_{CBO}	—	—	20 5.0	nA μA	$V_{CB} = 40\text{V}$ $V_{CB} = 40\text{V}, T_A = +125^\circ\text{C}$
Emitter-Cut Off Current	I_{EBO}	—	—	100	nA	$V_{EB} = 5.0\text{V}, I_C = 0$
Gain Bandwidth Product	f_T	100	—	—	MHz	$V_{CE} = 5.0\text{V}, I_C = 10\text{mA}, f = 100\text{MHz}$
Collector-Base Capacitance	C_{CBO}	—	2.0	3.0	pF	$V_{CB} = 10\text{V}, f = 1.0\text{MHz}$
Emitter-Base Capacitance	C_{EBO}	—	11	—	pF	$V_{EB} = 0.5\text{V}, f = 1.0\text{MHz}$

- Notes:
5. For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 6. Short duration pulse test used to minimize self-heating effect.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$ unless otherwise specified.)

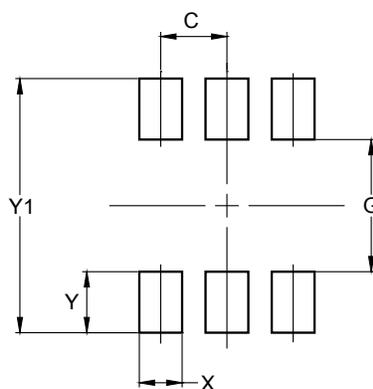


Package Outline Dimensions



SOT363			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	1.00
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500